

Graphene Transistors Based Microwave Amplifiers

Authors : Pejman Hosseinioun, Ali Safari, Hamed Sarbazi

Abstract : Graphene is a one-atom-thick sheet of carbon with numerous impressive properties. It is a promising material for future high-speed nanoelectronics due to its intrinsic superior carrier mobility and very high saturation velocity. These exceptional carrier transport properties suggest that graphene field effect transistors (G-FETs) can potentially outperform other FET technologies. In this paper, detailed discussions are introduced for Graphene Transistors Based Microwave Amplifiers.

Keywords : graphene, microwave FETs, microwave amplifiers, transistors

Conference Title : ICE 2014 : International Conference on Electronics

Conference Location : Paris, France

Conference Dates : December 30-31, 2014